



PJM9926ANPA

Dual N-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = 20V, I_D = 6A$
- $R_{DS(on)} < 28m\Omega @ V_{GS} = 4.5V$
- $R_{DS(on)} < 38m\Omega @ V_{GS} = 2.5V$

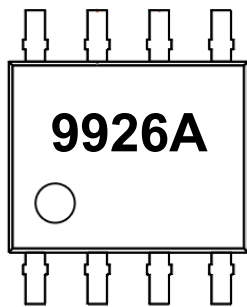
Features

- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

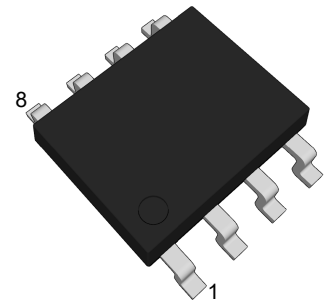
Application

- Power Switching Application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

Marking Code



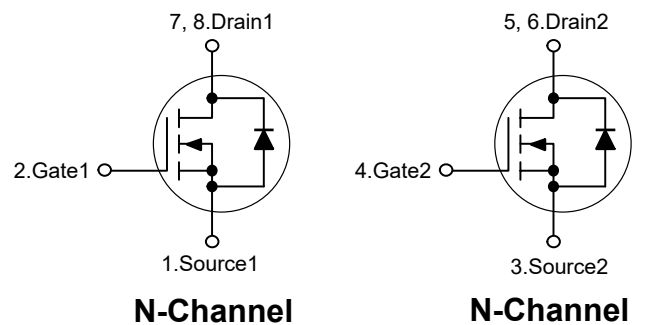
SOP-8



(Top View)

Pin	Description	Pin	Description
1	Source1	4	Gate2
2	Gate1	5,6	Drain2
3	Source2	7,8	Drain1

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	6	A
Drain Current-Pulsed ^{Note1}	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.8	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	83	°C/W
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Electrical Characteristics

(T_J=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	20	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	1.2	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =4.5V, I _D =6A	--	24	28	mΩ
		V _{GS} =2.5V, I _D =5A	--	33	38	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	640	--	pF
Output Capacitance	C _{oss}		--	140	--	pF
Reverse Transfer Capacitance	C _{rss}		--	80	--	pF
Total Gate Charge	Q _g	V _{DD} =10V, V _{GS} =4.5V, I _D =4.3A	--	6.5	--	nC
Gate-Source Charge	Q _{gs}		--	1.6	--	nC
Gate-Drain Charge	Q _{gd}		--	1.5	--	nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DS} =10V, V _{GS} =4.5V, I _D =1A R _{GEN} =3Ω	--	8	--	nS
Turn-on Rise Time	t _r		--	58	--	nS
Turn-off Delay Time	t _{d(off)}		--	20	--	nS
Turn-off Fall Time	t _f		--	68	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V, I _S =6A	--	--	1.2	V
Diode Forward Current ^{Note2}	I _S		--	--	6	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2.Surface Mounted on FR4 Board, t ≤ 10 sec.

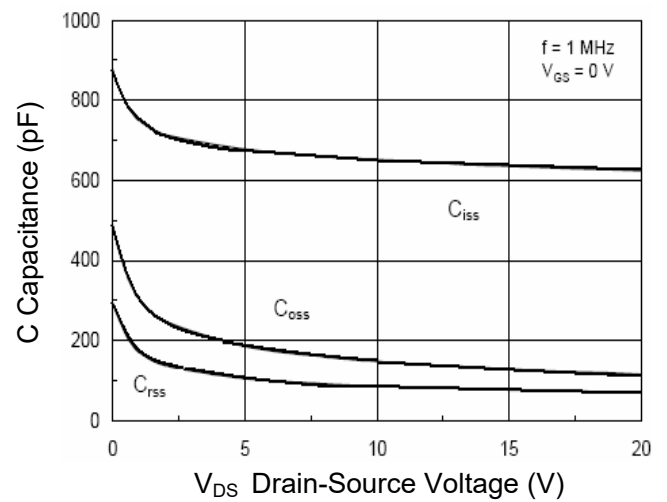
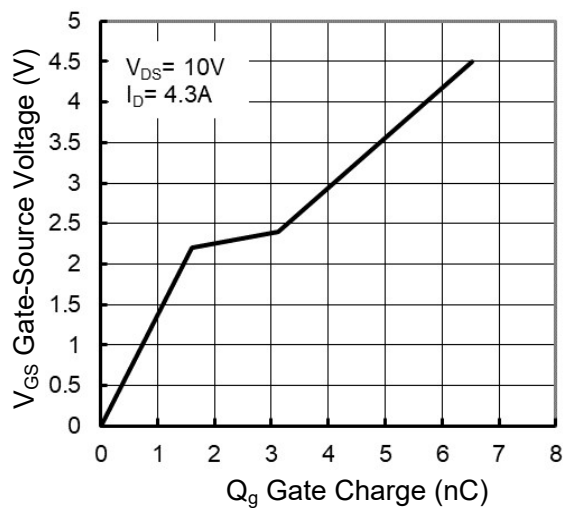
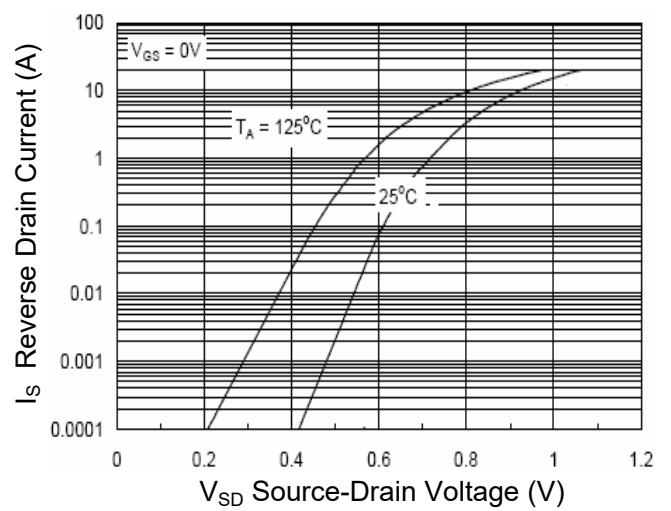
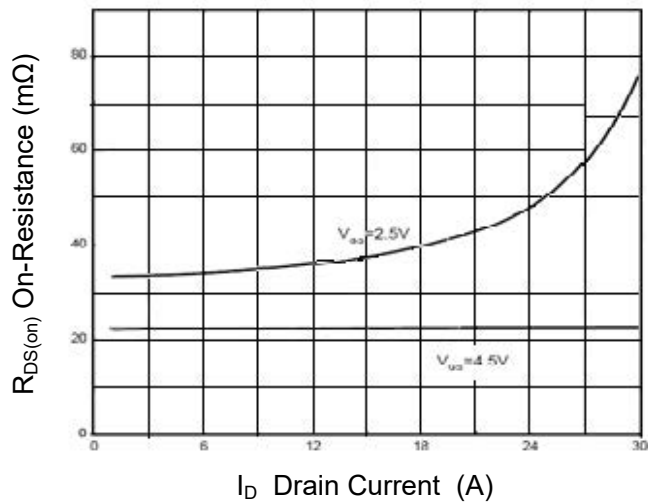
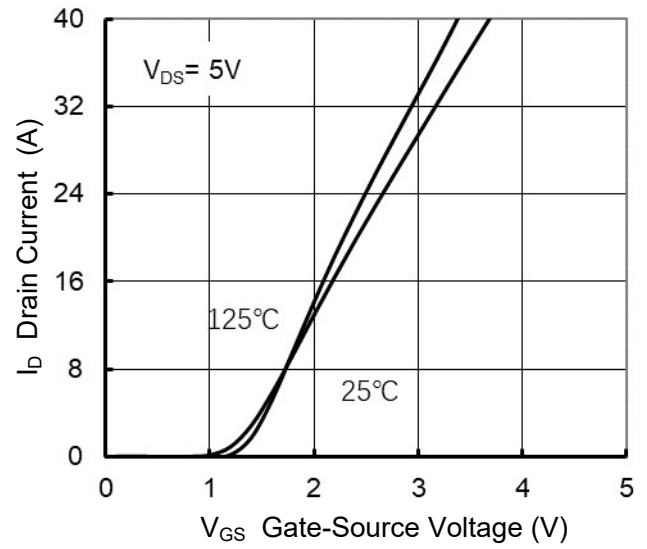
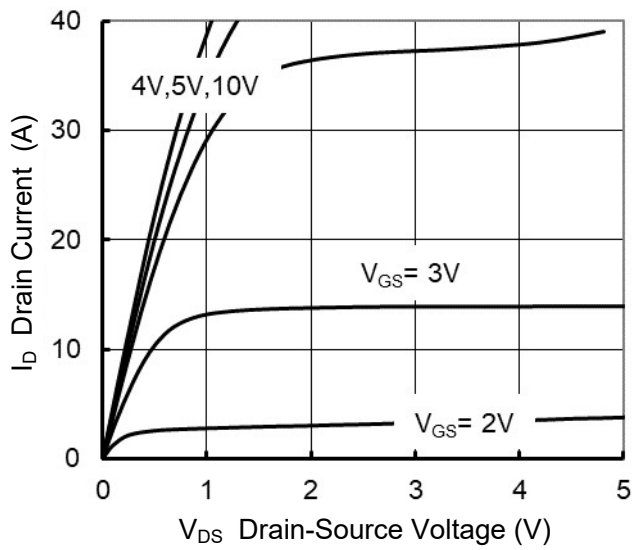
3.Pulse Test: Pulse width≤300μs, duty cycle≤0.5%



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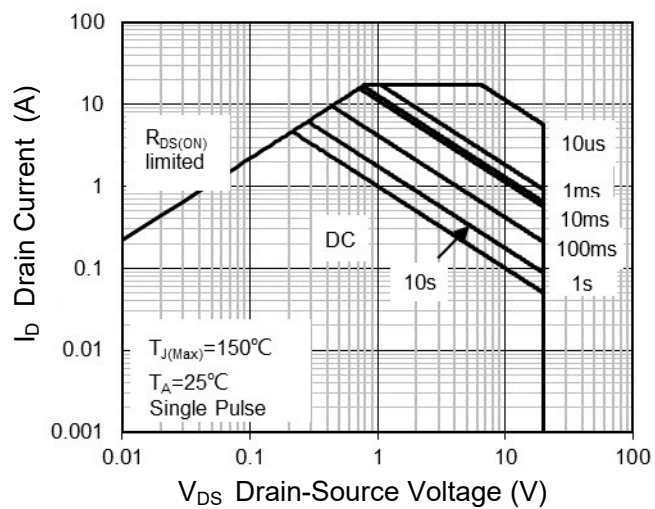
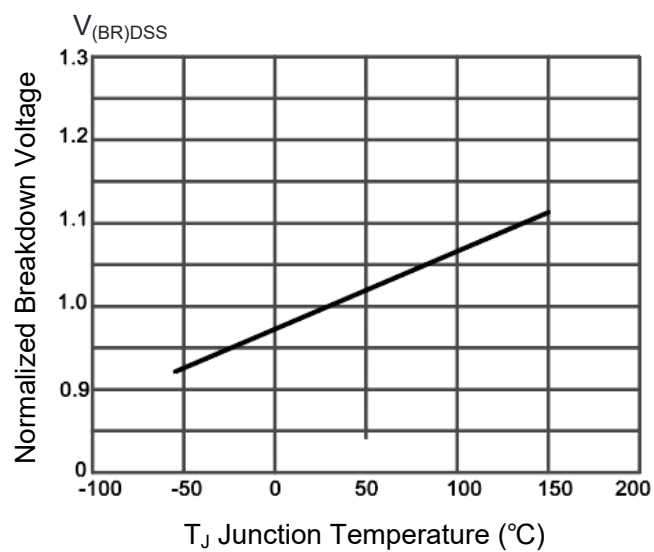
Typical Characteristic Curves





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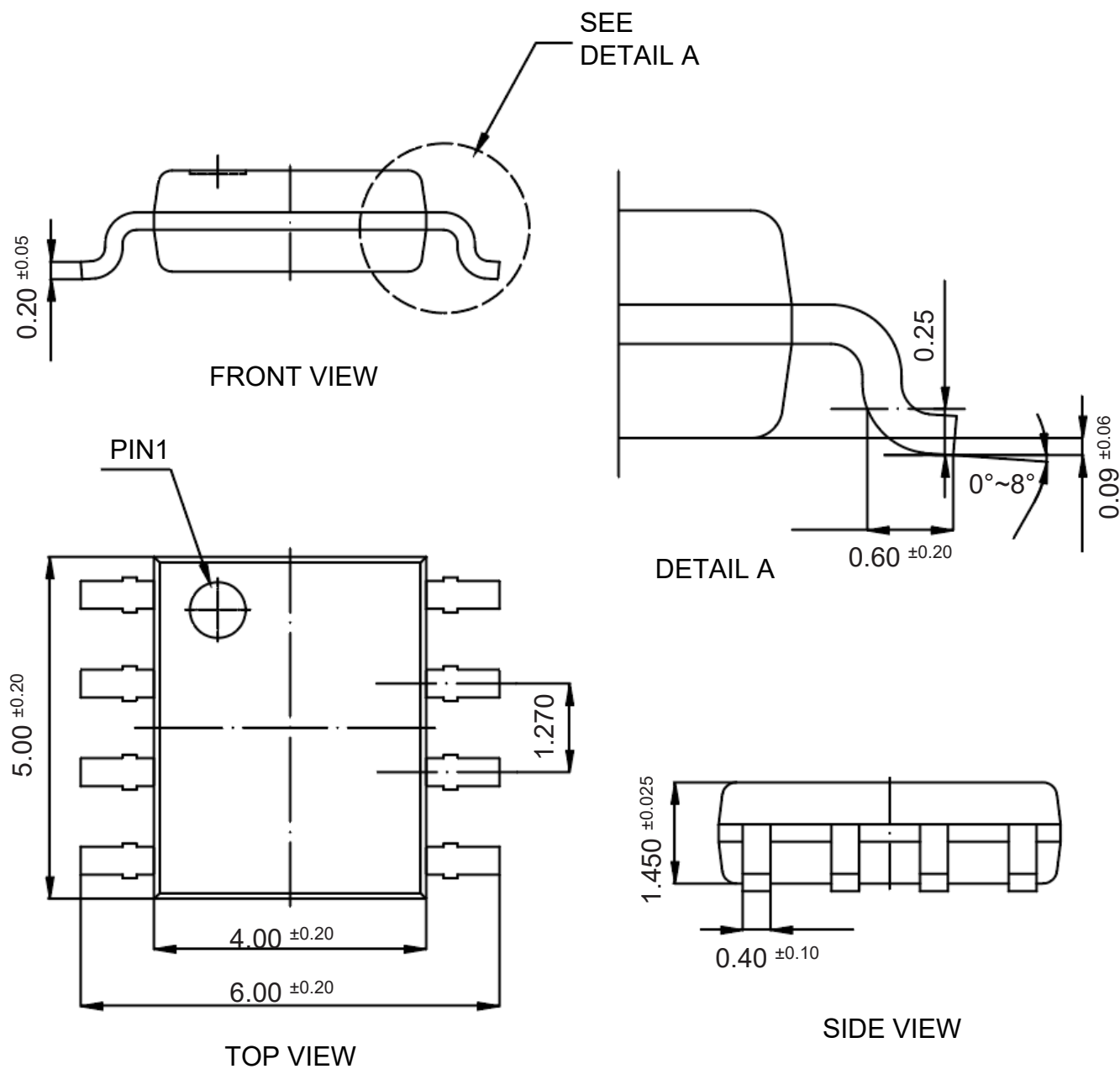
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Package Outline

SOP-8

Dimensions in mm



Ordering Information

Device	Package	Shipping
PJM9926ANPA	SOP-8	4,000PCS/Reel&13inches